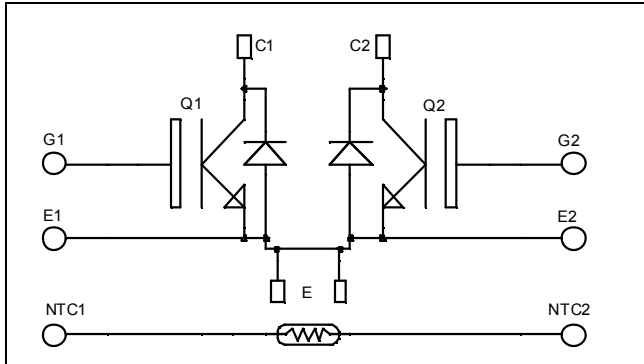


**Dual common source
Trench + Field Stop IGBT®
Power Module**

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**$V_{CES} = 600V$
 $I_C = 200A @ T_c = 80^\circ C$**

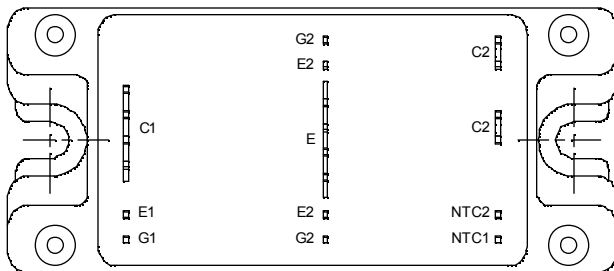


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCESat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	290
		$T_c = 80^\circ C$	200
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	625
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	400A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 200\text{A}$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 150^\circ\text{C}$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2\text{mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		12.3		nF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		0.8		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.4		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 200\text{A}$ $R_G = 2\Omega$		115		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			225		
T_f	Fall Time			55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 200\text{A}$ $R_G = 2\Omega$		130		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			300		
T_f	Fall Time			70		
E_{on}	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 200\text{A}$	$T_j = 25^\circ\text{C}$	1		mJ
			$T_j = 150^\circ\text{C}$	1.8		
E_{off}	Turn off Energy	$R_G = 2\Omega$	$T_j = 25^\circ\text{C}$	5.7		mJ
			$T_j = 150^\circ\text{C}$	7		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 150^\circ\text{C}$		500	
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$	200		A
V_F	Diode Forward Voltage	$I_F = 200\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.6	2	V
			$T_j = 150^\circ\text{C}$	1.5		
t_{rr}	Reverse Recovery Time	$I_F = 200\text{A}$ $V_R = 300\text{V}$ $di/dt = 2200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	130		ns
			$T_j = 150^\circ\text{C}$	225		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	9		μC
			$T_j = 150^\circ\text{C}$	19		
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	2.3		mJ
			$T_j = 150^\circ\text{C}$	4.7		

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

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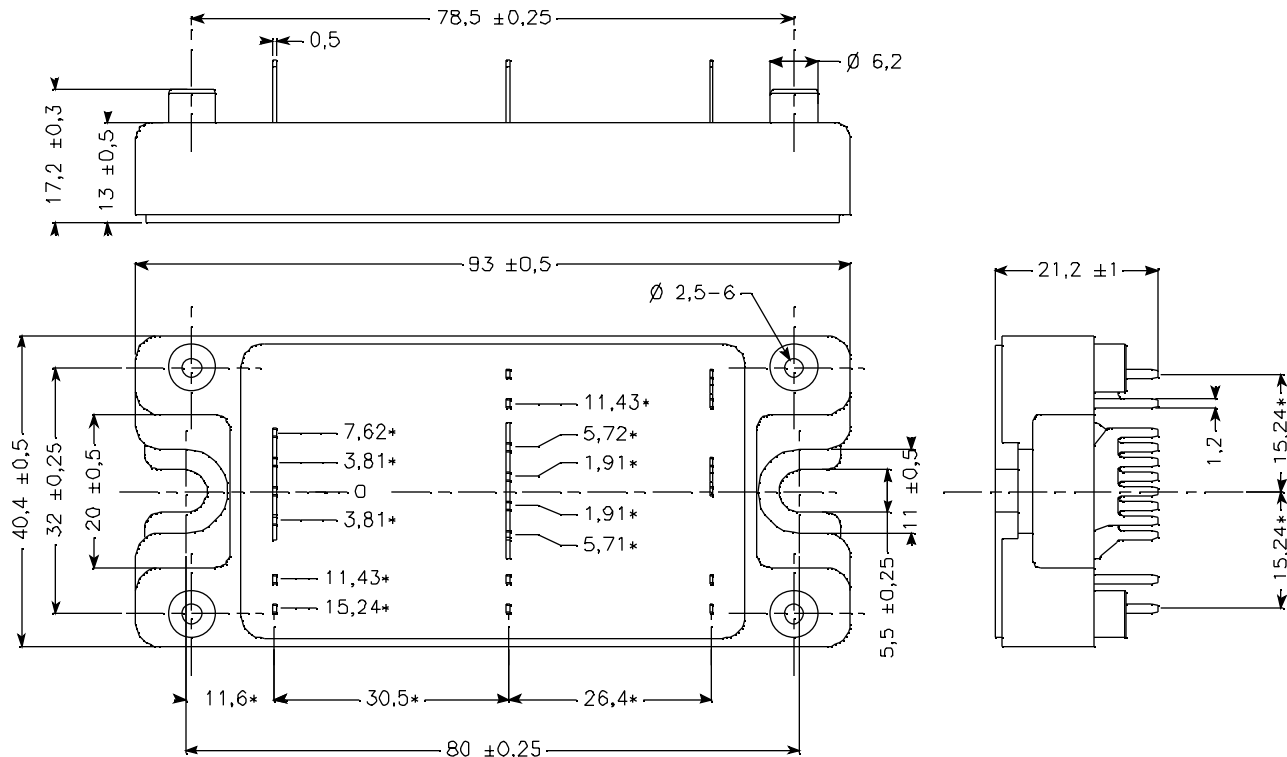
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit		
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.24	°C/W		
		Diode		0.4			
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V		
T _J	Operating junction temperature range	-40		175	°C		
T _{STG}	Storage Temperature Range	-40		125			
T _C	Operating Case Temperature	-40		100			
Torque	Mounting torque		To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)

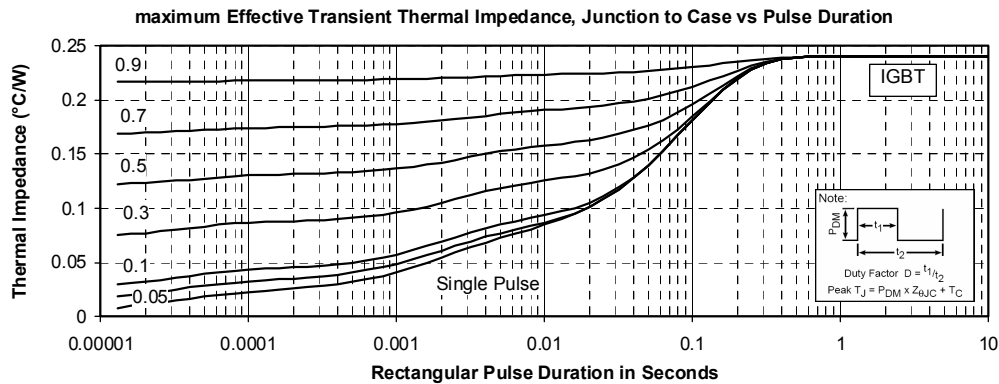
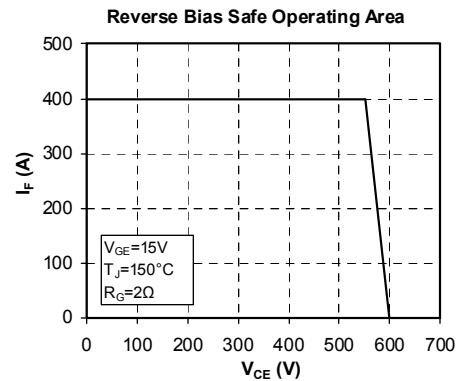
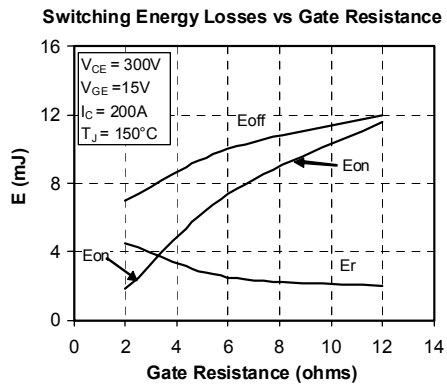
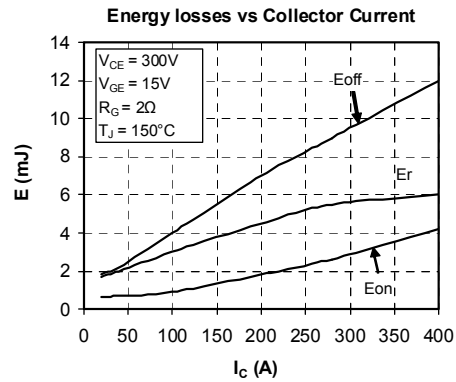
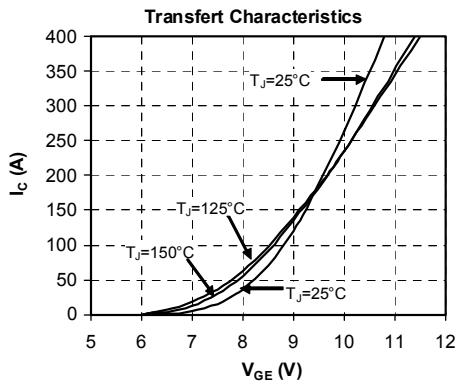
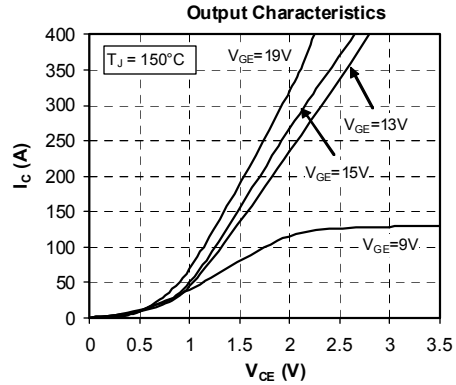
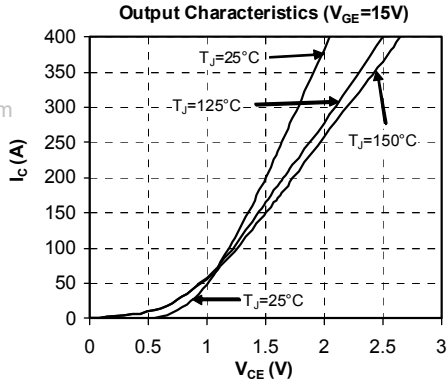


ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS: ± 0.1

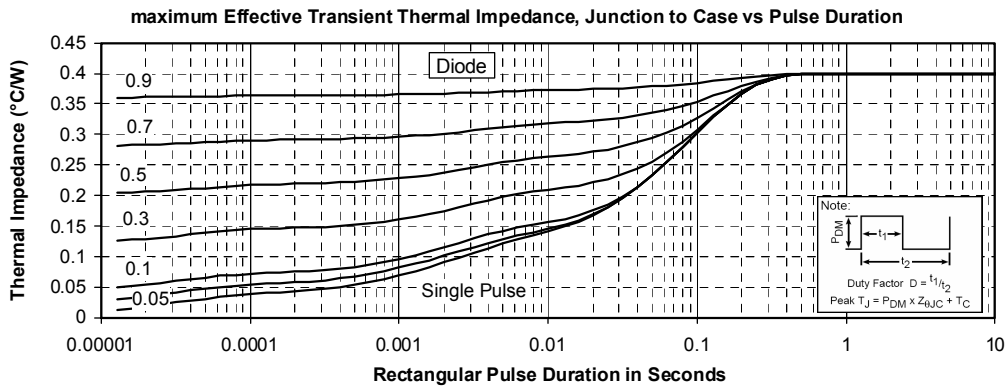
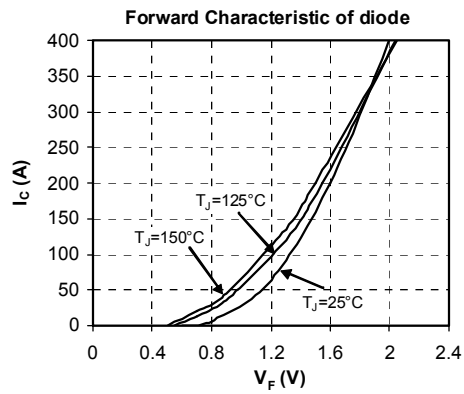
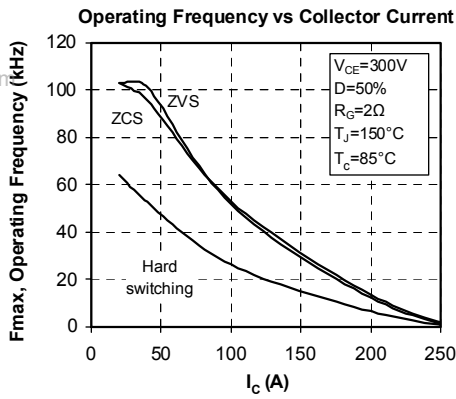
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve

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